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Overa	 cıu	IIL.

Between 0.325 inches and 0.400 inches

Body Length:

1.280 inches

Body Width:

Between 0.220 inches and 0.310 inches

Body Height:

Between 0.140 inches and 0.185 inches

Maximum Power Dissipation Rating:

1.2 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Bipolar and monolithic and programmable

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

20 input

Case Outline Source And Designator:

D-9 mil-m-38510

Current Rating Per Characteristic:

100.00 milliamperes forward current, nonrepetitive, peak total value

Terminal Surface Treatment:

Solder

Product Name:

20-input 8-output and-or invert gate array

Voltage Rating And Type Per Characteristic:

7.0 volts power source

Time Rating Per Chacteristic:

50.00 nanoseconds propagation delay time, low to high level output and 50.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Pal

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

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N/a

Unit Of Measure:

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Demilitarization:

No

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